

SANYO Semiconductors DATA SHEET

LB11988H -- Monolithic Digital IC Fan Motor Driver

Overview

The LB11988H is a motor driver IC optimal for driving the DC fan motors.

Features

- 3-Phase full-wave current-linear drive system.
- Current limiter circuit built in.
- Output stage upper/lower over-saturation prevention circuit built in.
- Forward/backward rotation direction setting circuit built in.
- FG amplifier built in.
- Thermal shutdown circuit built in.

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V _{CC} max		24	V
	VS max		24	V
Maximum output current	I _O max		1.3	А
Allowable power dissipation	Pd max	Independent IC	0.8	W
Operating temperature range	Topr		-30 to +85	°C
Storage temperature range	Tstg		-55 to +150	°C

Allowable Operating Range at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	VS		5 to 22	N/
	VCC		7 to 22	V
Hall input amplitude	VHALL	Between hall inputs	±30 to ±80	mVo-p

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LB11988H

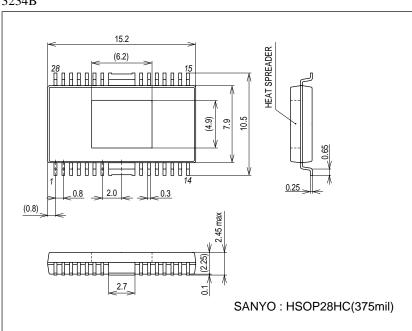
Electrical Characteristics at $Ta = 25^{\circ}C$, $V_{CC} = 12V$, VS = 12V

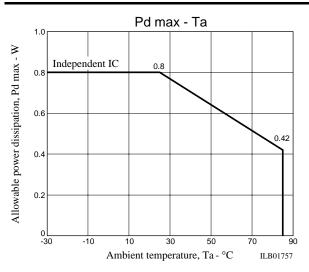
Deveryor	Symbol	Que ditions	Ratings			
Parameter		Conditions	min	typ	max	unit
V _{CC} supply current	ICC	R _L = 560Ω (Y)		15	24	mA
Output	·					
Output saturation voltage	V _O sat1	$I_O = 500$ mA, Rf = 0.5 Ω , Sink+Source (with saturation prevention)		2.1	2.6	
	V _O sat2	I_{O} = 1.0A, Rf = 0 Ω , Sink+Source (with saturation prevention)		2.6	3.5	V
Output leakage current	lOleak				1.0	mA
Hall amplifier						
Input offset voltage	Voff(HALL)		-6		+6	mV
Input bias current	lb(HALL)	V _{IN} , W _{IN}		1	3	μA
Common-mode input voltage	Vcm(HALL)		3		V _{CC} -3	V
FR						
Threshold voltage	VFRTH		4		8	V
Input bias current	lb(FR)		-5			μA
Current limit						
LIM pin current limit level	ILIM	Rf = 0.5Ω , Hall input logic fixed (U, V, W = H, H, L)		1		А
Saturation	·					
Saturation prevention circuit lower set voltage	V _O sat(DET)	$R_L = 560\Omega$ (Y), $Rf = 0.5\Omega$ Voltage between each OUT and RF		0.28		V
FG Amplifier						
Output "High" voltage	Vfgoh(SH)		11.8			
Output "Low" voltage	Vfgol(SH)				0.3	V
Hysteresis width	Vhys			23		mV
TSD operating temperature	TTSD	Design target value*		170		°C

*: T-TSD is not measured because it stands for design target.

Package Dimensions

unit : mm (typ) 3234B



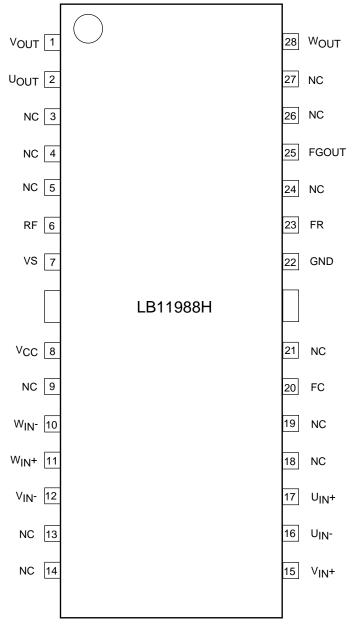


Truth Table and Control Function

			50			
	Source \rightarrow Sink	U	V	W	FR	
	$V\toW$		н	L	Н	
1	$W\toV$	Н			L	
2	$U\toW$		L	L	н	
	$W\toU$	Н			L	
	$U\toV$		L	н	н	
3	$V\toU$	Н			L	
	$W\toV$		L	н	н	
4	$V\toW$	L			L	
_	$W\toU$		н	Н	н	
5	$U\toW$	L			L	
6	$V \rightarrow U$	L	н	L	н	
	$U\toV$				L	

- Note: "H" in the FR column represents a voltage of 8V or more. "L" represents a voltage of 4V or less. (At V_{CC}=12V)
- Note: "H" under the Hall Input columns represents a state in which "+" has a potential which is higher by 0.01V or more than that of the "-" phase inputs. Conversely "L" represents a state in which "+" has a potential which is lower by 0.01V or more than that of the "-" phase inputs.
- Note: Since a 180° energized system is used as a drive system, other phases than the sink and source are not OFF.

Pin Assignment



Top view

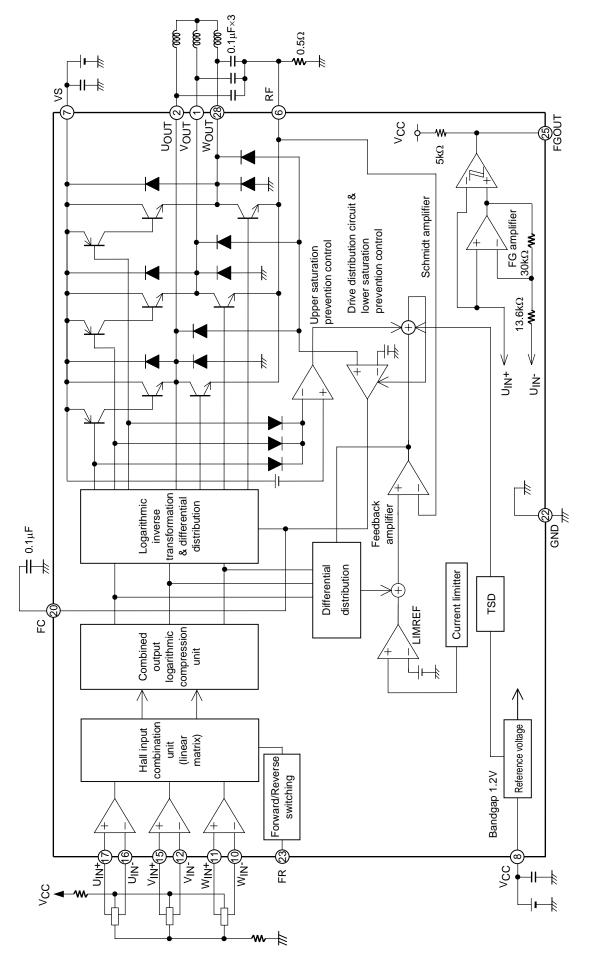
Pin Functions

Pin Name	Pin No.	Input/Output Equivalent Circuit	Pin Functions
GND	22		GND for others than the output transistor.
	FRAME		Minimum potential of output transistor is at RF pin.
FGOUT	25	VCC GY VCC C VCC C VCC C VCC C VCC C VCC C VCC C VCC C VCC C VCC C VCC	FG amplifier output pin. Resistive load provided internally.
FR	23	FR 23	Forward/Reverse switching pin.
FC	20	VCC Gy Cy TTT TTT TTT TTT TTT TTT TTT TTT TTT	Frequency characteristics compensation pin for over-saturation prevention circuit loop.
U _{IN} +, U _{IN} -	17,16	Each (+) input (17) Each (-) input (16)	U-phase Hall device input pin; logic "H" presents IN+>IN-
V _{IN} +, V _{IN} -	15,12	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V-phase Hall device input pin; logic "H" presents IN+>IN-
W _{IN} +,W _{IN} -	11,10		W-phase Hall device input pin; logic "H" presents IN+>IN-
V _{CC}	8		Power supply pin for supplying power to all circuits expect output section in IC; this voltage must be stabilized so as to eliminate ripple and noise.

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Pin Name	Pin No.	Input/Output Equivalent Circuit	Pin Functions
U _{OUT} Vout Wout	2 1 28		U-phase output pin. V-phase output pin. W-phase output pin. (Built-in spark killer diode)
RF	6	7 VS VCC Each OUT Each OUT 2 1 2 1 2 1 2 1 2 1 2 1 2 1 2 1 8 200Ω 7 VCC 9 1 9 1 9 1 10 1 <td>Output current detection pin. Connecting Rf between this pin and GND activates current limiting circuit. Then the lower over-saturation prevention circuit is activated in accordance with this pin voltage. Since the over-saturation prevention level is set with this voltage, the lower over-saturation prevention effect may deteriorate in the high current range if the Rf value is reduced to an extremely low level.</td>	Output current detection pin. Connecting Rf between this pin and GND activates current limiting circuit. Then the lower over-saturation prevention circuit is activated in accordance with this pin voltage. Since the over-saturation prevention level is set with this voltage, the lower over-saturation prevention effect may deteriorate in the high current range if the Rf value is reduced to an extremely low level.
VS	7		Power supply pin for supplying power to output section in IC.

Block Diagram



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